

## BROAD AREA LASER

GaAs Semiconductor Laser Diode  
Single Emitter Structure



### PRELIMINARY SPECIFICATION

### BA Laser

## EYP-BAL-0808-08000-4020-CMT04-0000

### General Product Information

Product	Application
808 nm Broad Area Laser	Material Processing
mounted on C-Mount	Medical



### Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	$T_S$	°C	-40		85
Operational Temperature at Case	$T_C$	°C	5		40
Forward Current	$I_F$	A			13
Reverse Voltage	$V_R$	V			0
Output Power	$P_{opt}$	W			9

#### Measurement Conditions / Comments

non condensing

non condensing

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device reliability and may lead to reduced operational life.

### Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	$T_C$	°C	15		30
Forward Current	$I_F$	A			12
Output Power	$P_{opt}$	W			8

#### Measurement Conditions / Comments

measured at position A (see drawing on p. 3)

### Characteristics at $T_{amb} 25\text{ °C}$ at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	$\lambda_C$	nm	793	808	823
Spectral Width (FWHM)	$\Delta\lambda$	nm			6
Temperature Coefficient of Wavelength	$d\lambda / dT$	nm / K		0.4	
Output Power @ $I_F = 12\text{ A}$	$P_{opt}$	W	8		
Slope Efficiency	$\eta_d$	W / A	0.7	0.9	
Threshold Current	$I_{th}$	A			2.5

#### Measurement Conditions / Comments

see images on page 4

total output measured with integrating sphere



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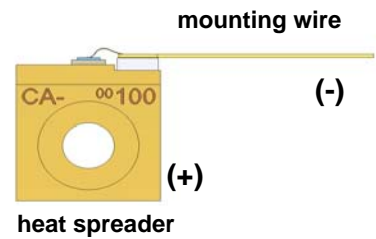
**EYP-BAL-0808-08000-4020-CMT04-0000**

**Package Dimensions**

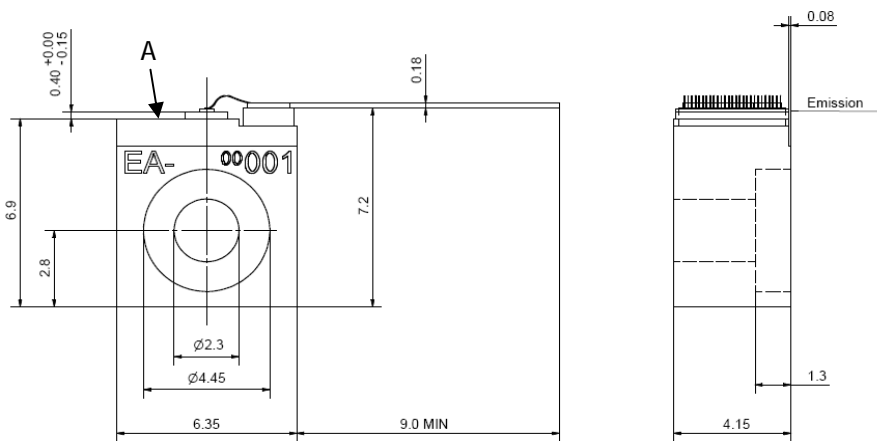
	Symbol	Unit	min	typ	max
Emission Plane	l	mm	7.05	7.20	7.35
C-Mount Thickness	d	mm		4	

**Package Pinout**

Cathode (-)	Mounting Wire
Anode (+)	Housing



**Package Drawings**



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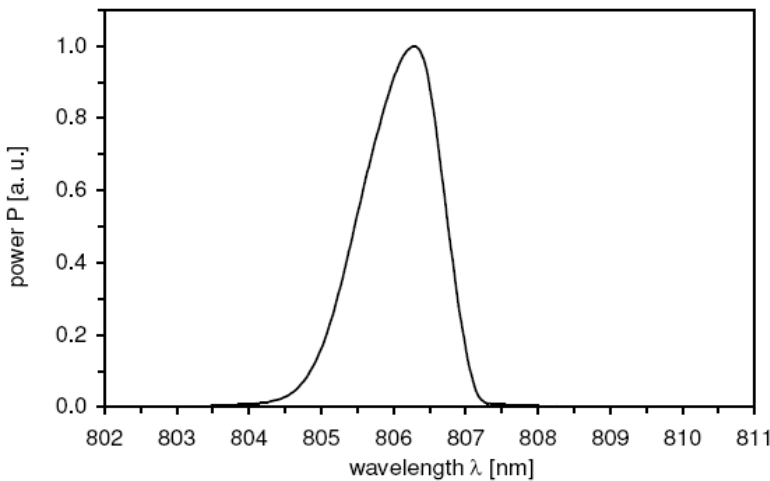
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**Typical Measurement Results**

Spectrum at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

*Ordering Information:*



800 Village Walk #316  
Guilford, CT 06437  
Ph: 203-401-8093

Email orders to: [sales@xsoptix.com](mailto:sales@xsoptix.com)  
Fax orders to: 800-878-7282

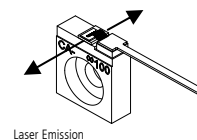
**Unpacking, Installation and Laser Safety**

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The BAL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



Laser Emission

